



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re ~~PATENT~~ APPLICATION OF

Tomohisa HOSHINO et al.

Appln. No.: 09/835,820

Filed: April 17, 2001

Title: FABRICATION PROCESS OF A SEMICONDUCTOR DEVICE INCLUDING A CVD  
PROCESS OF A METAL FILM

Confirmation No.: 5539

Group Art Unit: 2825

Examiner: LUU, Chuong A

7/A Amolt  
4/19/02  
A.Weller

April 16, 2002

\* \* \* \* \*

AMENDMENT

RECEIVED  
TECHNOLOGY CENTER 2800  
APR 17 2002

Hon. Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated January 16, 2002, please amend the above identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

A' 2. (Amended) A method as claimed in claim 1, wherein said first reducing gas atmosphere is selected from the group consisting of: silane, ammonia and hydrogen.

A' 4. (Amended) A method as claimed in claim 1, wherein said second reducing gas atmosphere includes hydrogen.

See the attached Appendix for the changes made to effect the above claim(s).